

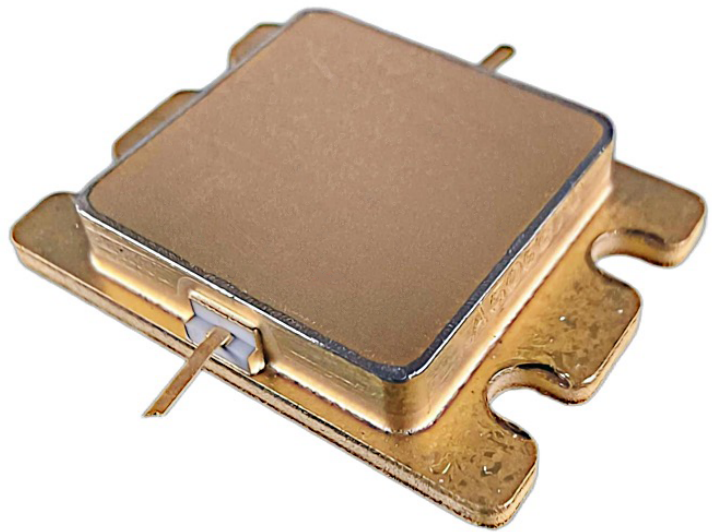
SANCOM

SA-PA020022-P42-1

2.0-2.2 GHz High Power GaAs-HEMT

Features

Frequency Range: 2.0 - 2.2 GHz

 $P_{1dB} : \geq 42 \text{ dBm}$ Power Gain: $\geq 11 \text{ dB}$ Efficiency: $\geq 45\%$ $Z_{in} / Z_{out} = 50 \Omega$ 

Description

Sancom Electric's GaAs-HEMT SA-PA020022-P42-1 offers high power, high efficiency, ease of matching and greater consistency for high power applications with 10V operation. The SA-PA020022-P42-1 typically provides 42 dBm of 1dB output power and 11 dB of large-signal gain and can be widely used in various RF/microwave systems.

ABSOLUTE MAXIMUM RATINGS

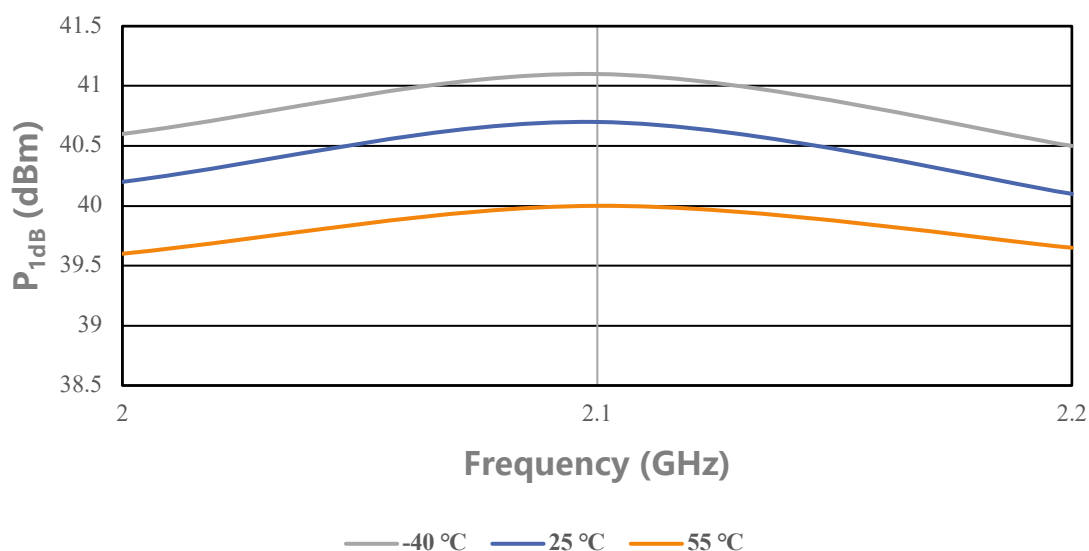
Parameter	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}	TC=25°C	11	V
Gate-Source Voltage	V_{GS}	TC=25°C	-5	V
Storage Temperature	T_{stg}	TC=25°C	-65 to 150	°C
Channel Temperature	T_{ch}	TC=25°C	150	°C

ELECTRICAL SPECIFICATIONS

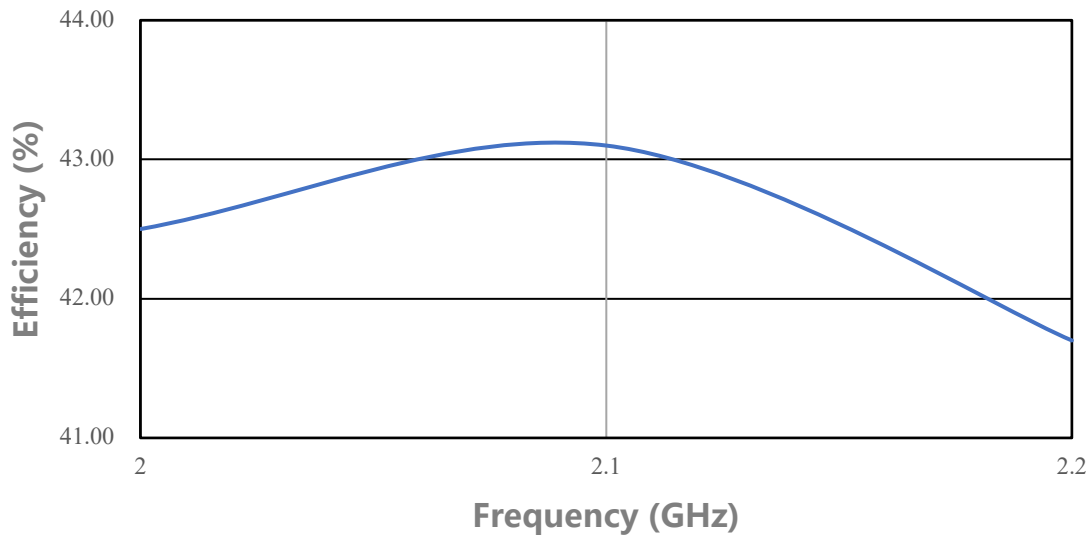
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Current	I_{DS}	V_{DS} : 10 V CW (Continuous Wave) P_{in} : 31 dBm Freq: 2.0 ~ 2.2 GHz	-	3.5	-	A
1dB Output	P_{1dB}		42	-	-	dBm
Power Gain	G_p		11	-	-	dB
Efficiency	η		45	-	-	%
Flatness	ΔG		-0.8	-	0.8	dB

Performance Plots

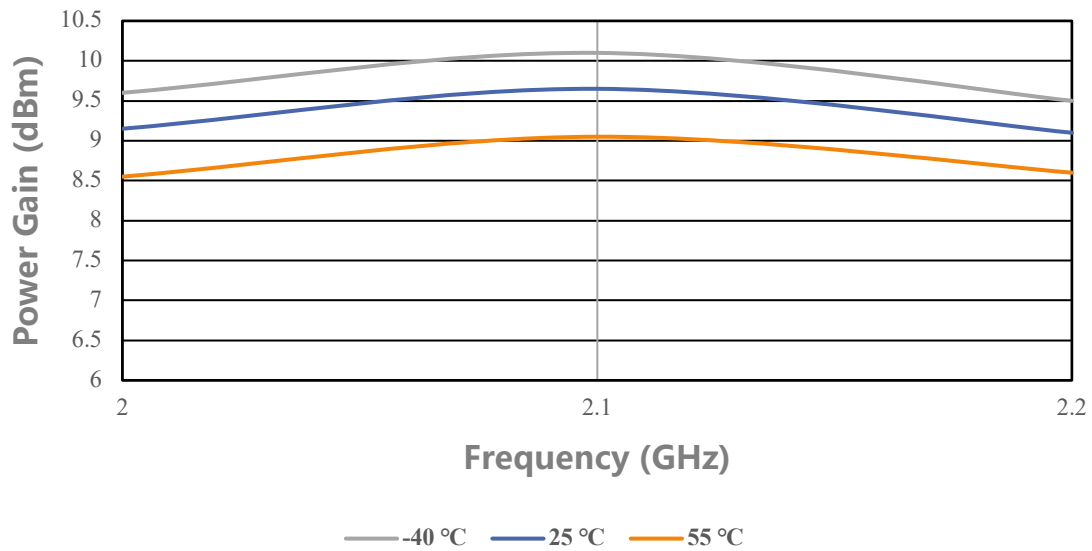
P_{1dB} VS Frequency



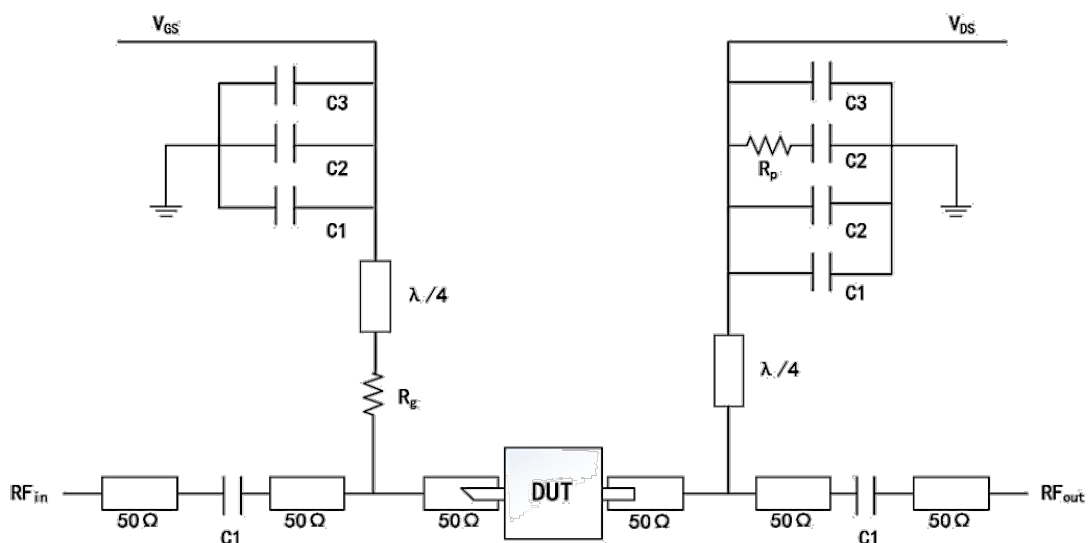
Efficiency VS Frequency



Power Gain VS Frequency



Simplified Block Diagram



DUT information	
C1: 8 pF	Rp: 51 Ω
C2: 1000 pF	Rg: 15 Ω
C3: 100 μF	

ESD Protection

ESD	Class III	2000 V
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Outline Drawing



Unit: mm

Attention

- Please keep away from moisture during transportation and storage
- Pay attention to ESD prevention during chip use and assembly. Wear a grounding ESD bracelet.
- When adding electricity, add gate electricity first and then add leakage electricity